

FIG. 1

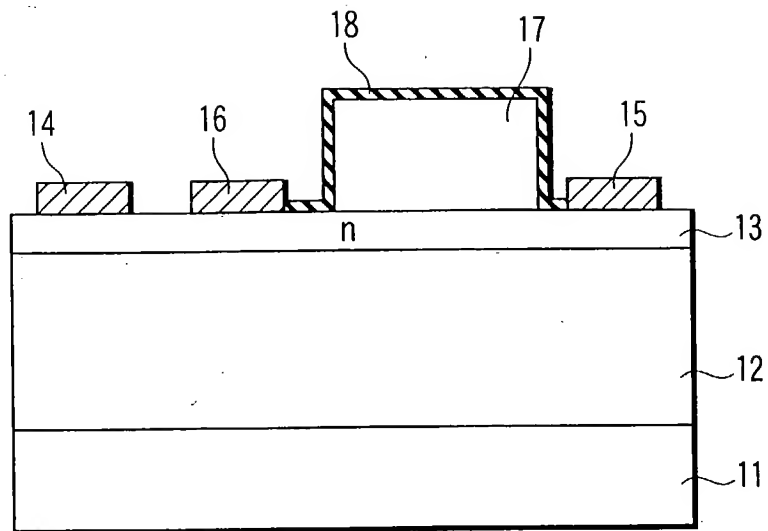


FIG. 2

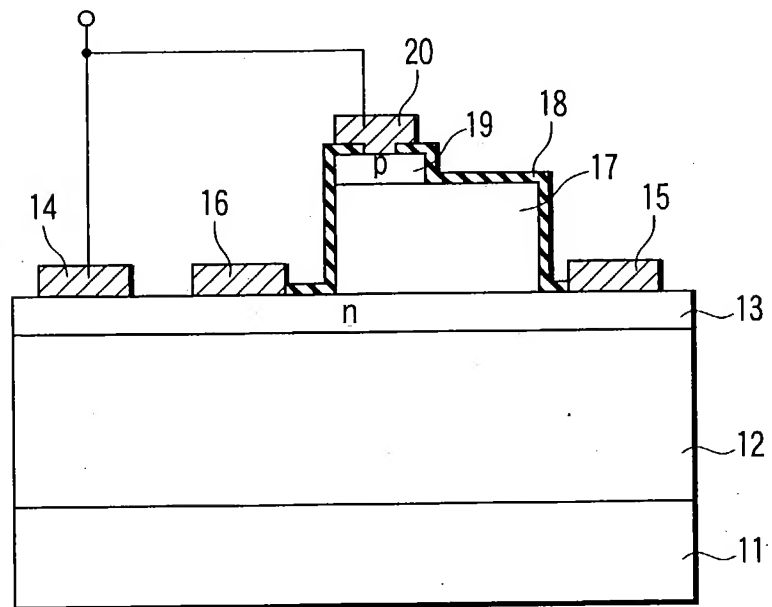


FIG. 3

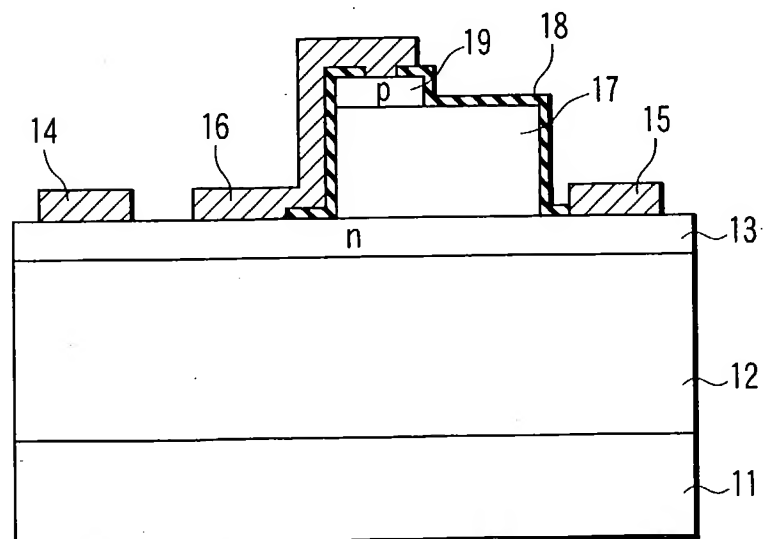


FIG. 4

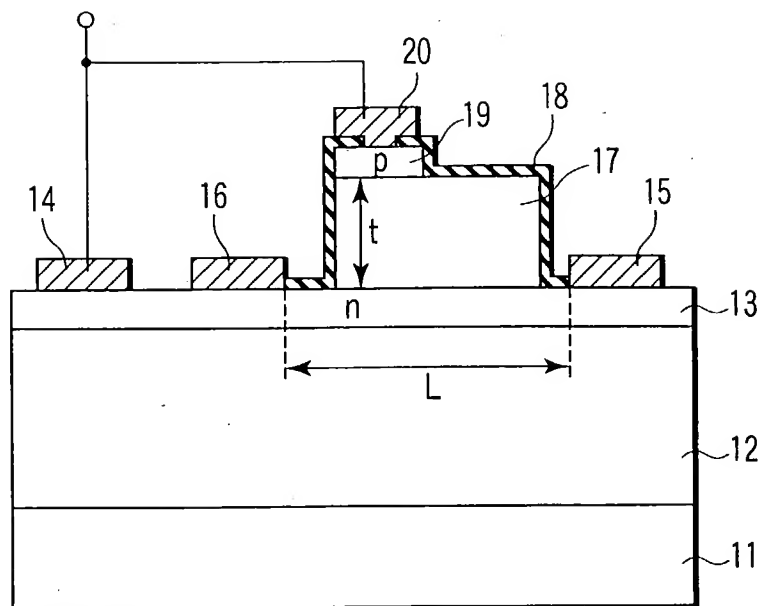


FIG. 5

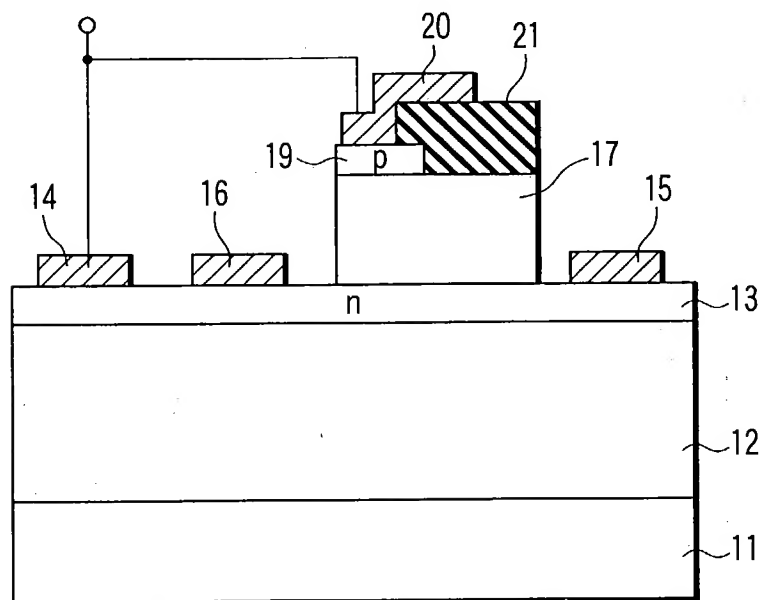


FIG. 6

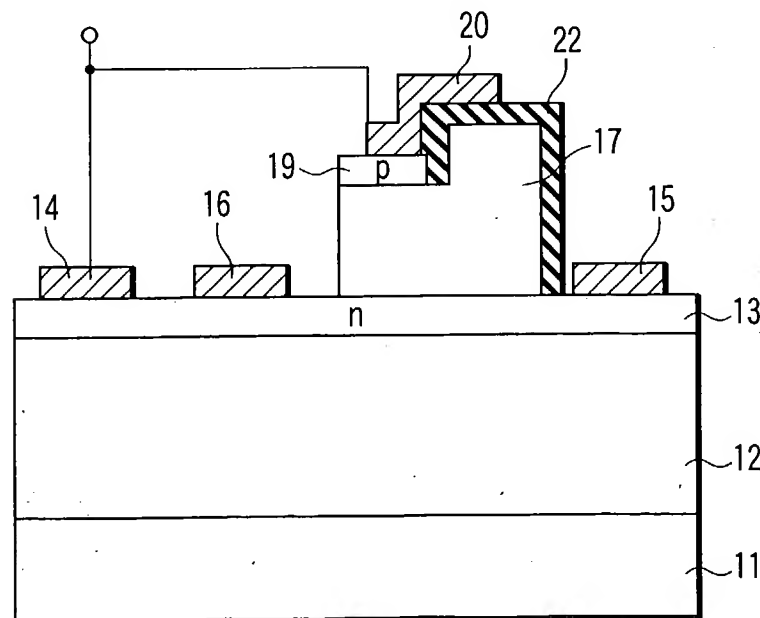


FIG. 7

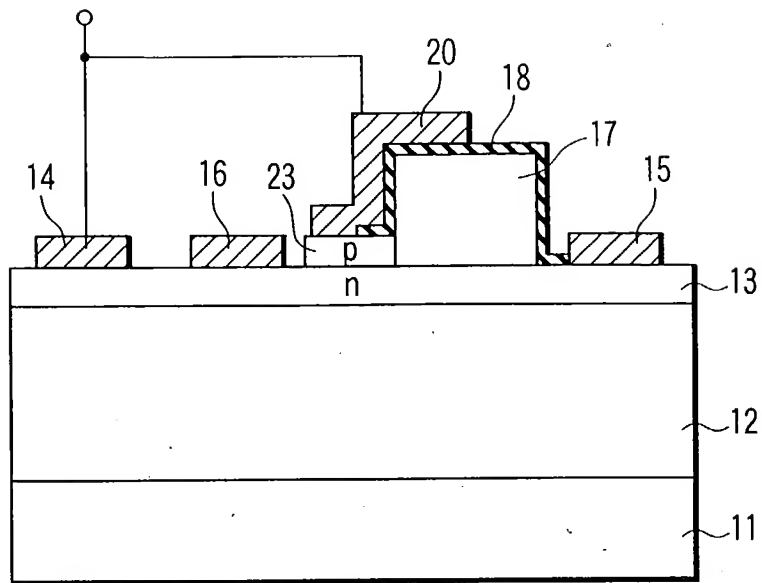


FIG. 8

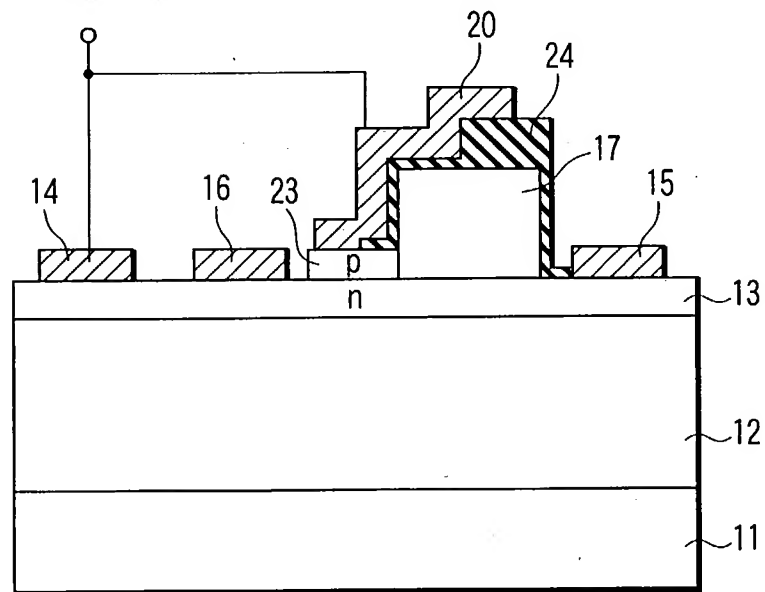


FIG. 9

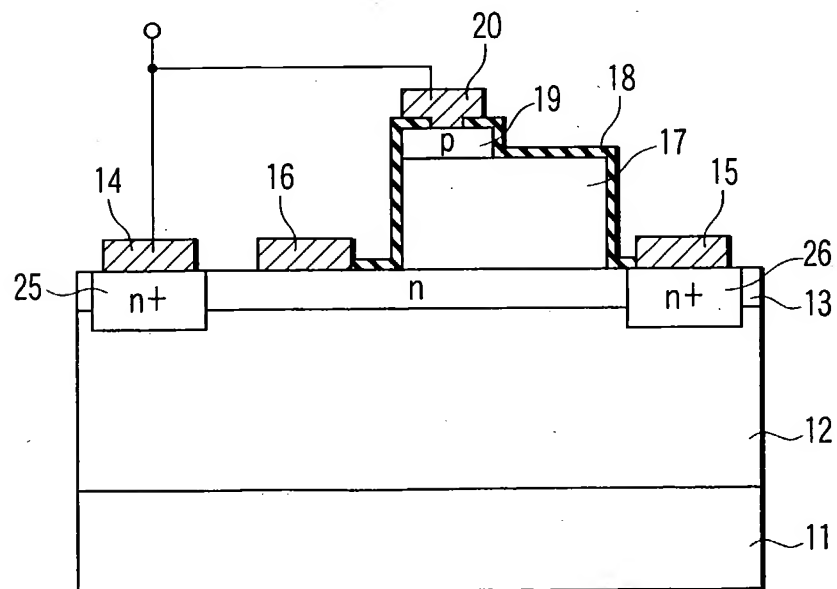


FIG. 10

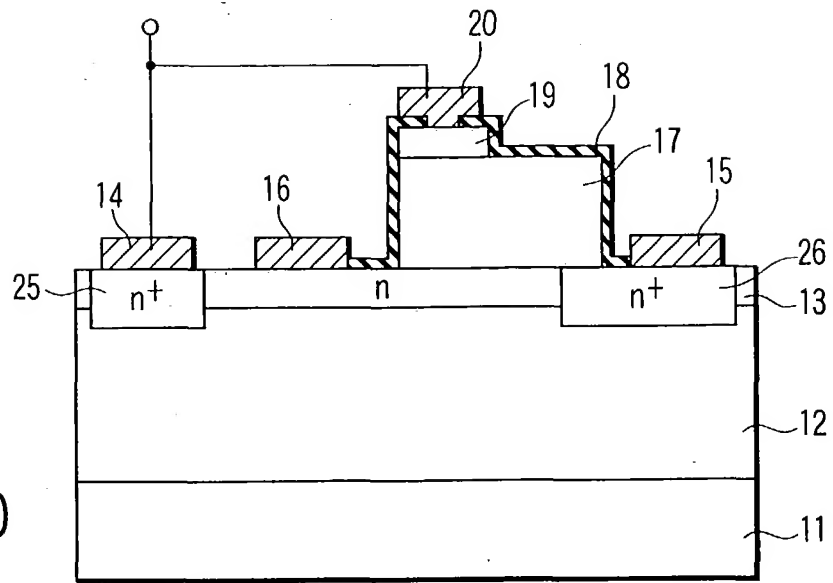


FIG. 11

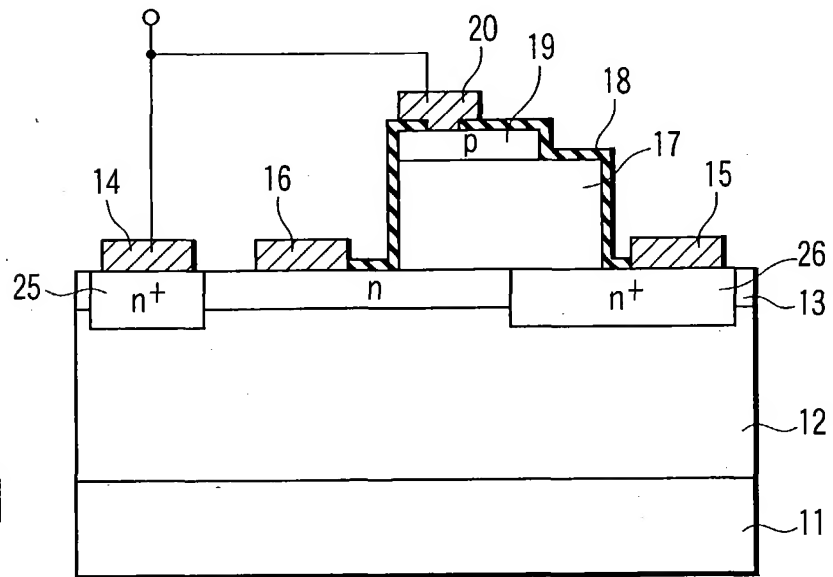


FIG. 12

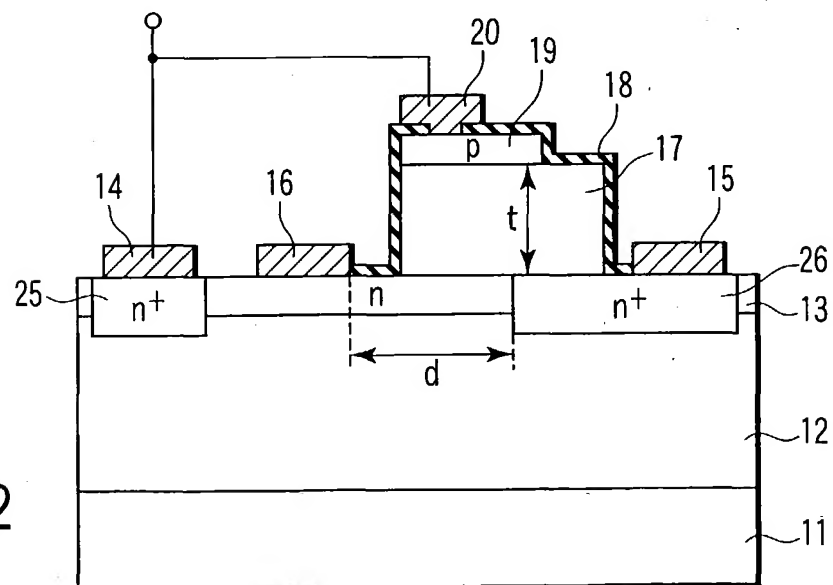


FIG. 13

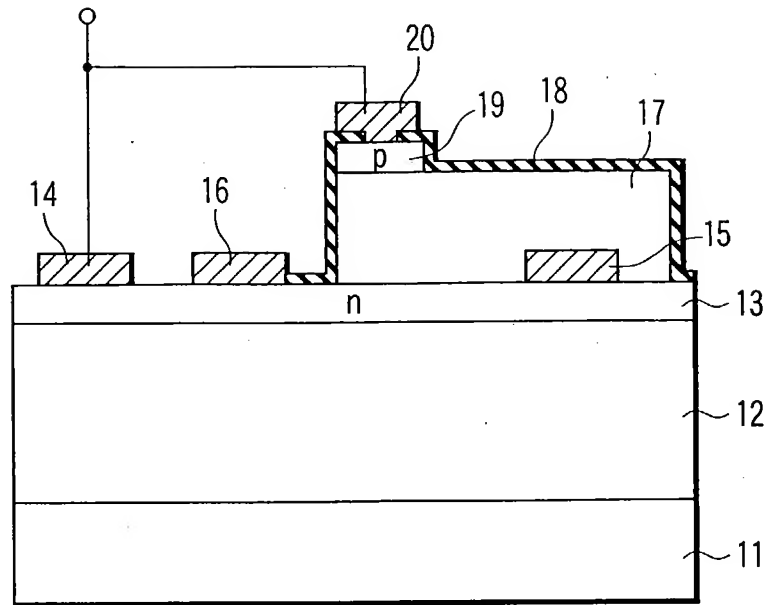


FIG. 14

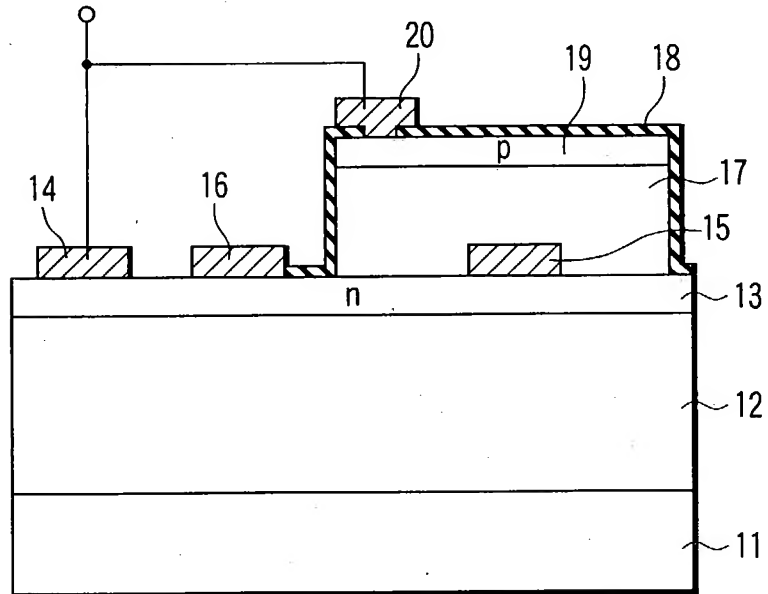


FIG. 15

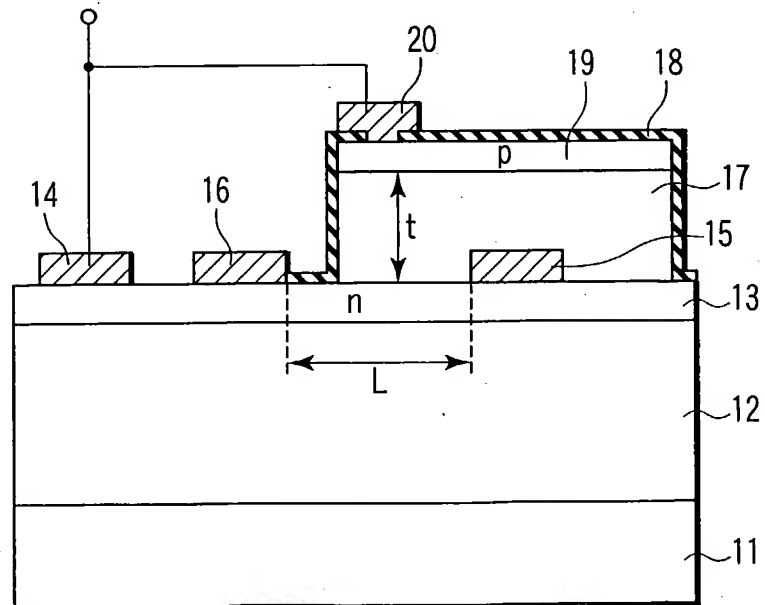


FIG. 16

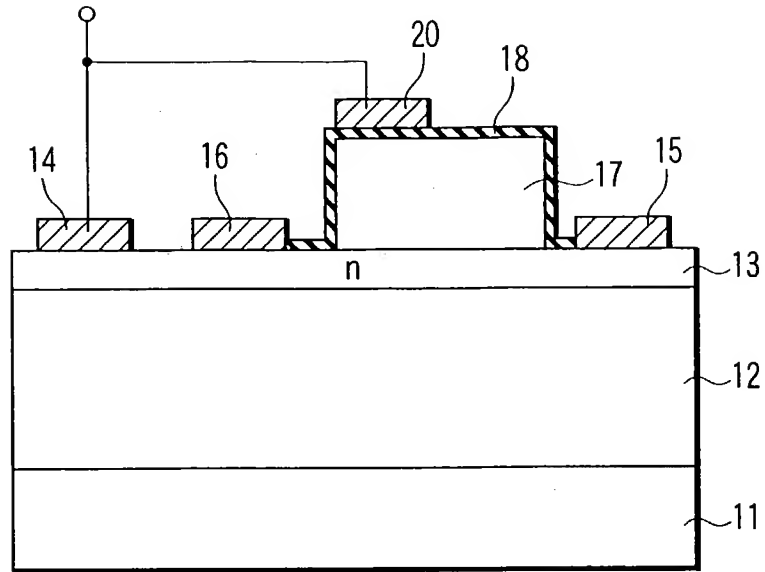


FIG. 17

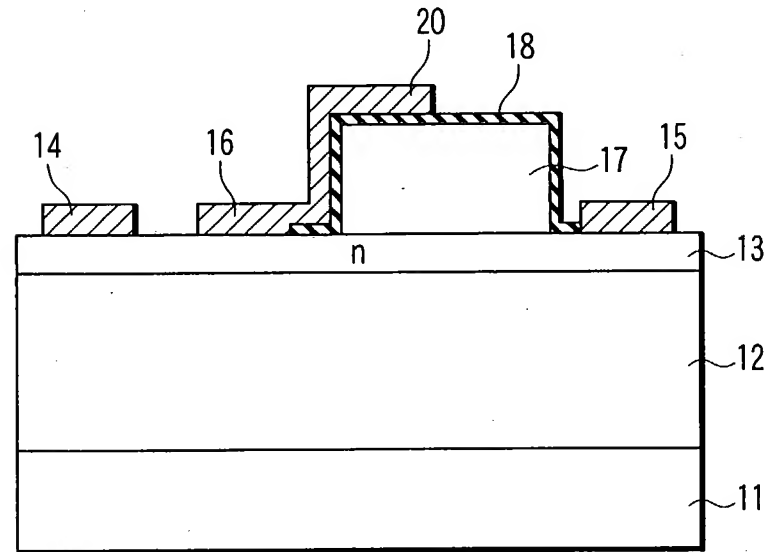
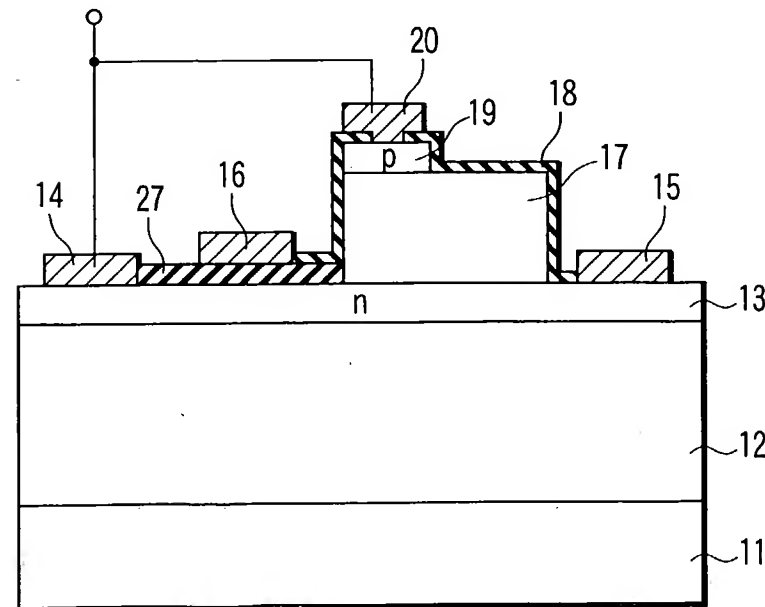


FIG. 18



A cross-sectional diagram of a GaN-based device structure. The structure consists of several layers: a bottom GaN layer (12), a p-GaN layer (19) on top of it, and a top n-AlGaN layer (31). A layer of undoped AlGaN (32) is located between the p-GaN layer (19) and the n-AlGaN layer (31). The diagram is labeled with 'A' on the left and 'A'' on the right. The layers are labeled as follows: 12: GaN layer, 19: p-GaN layer, 31: n-AlGaN layer, and 32: Undoped AlGaN layer.

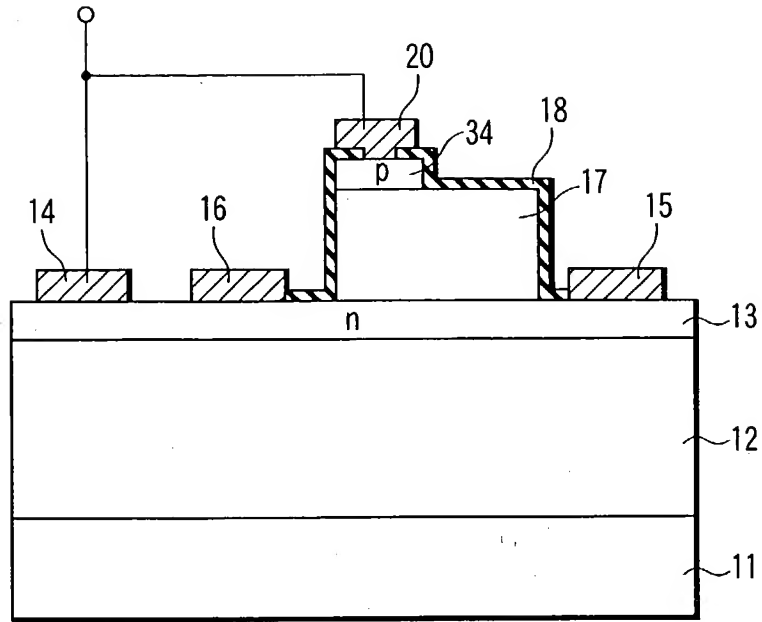


FIG. 21

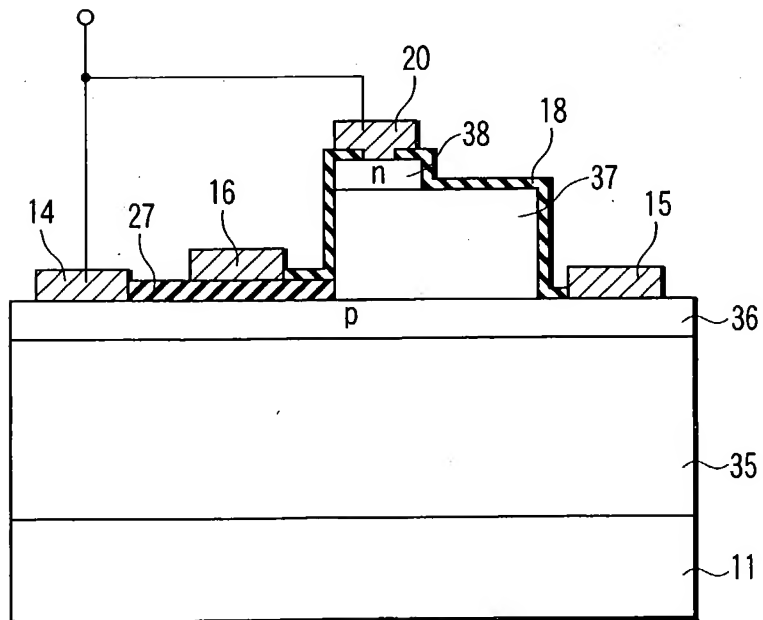


FIG. 22



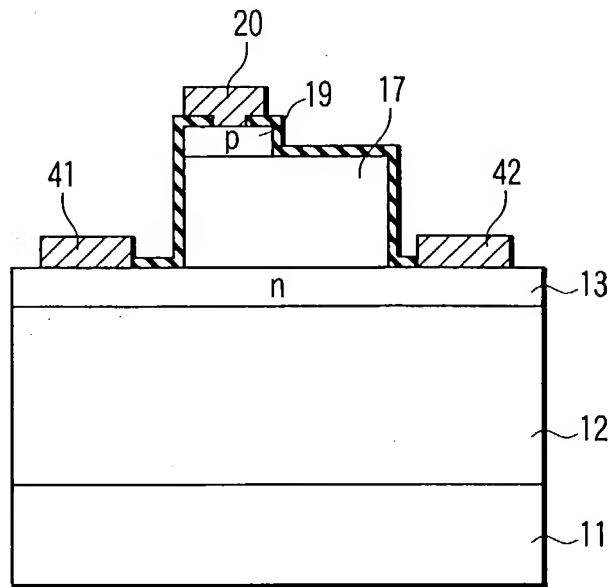


FIG. 23

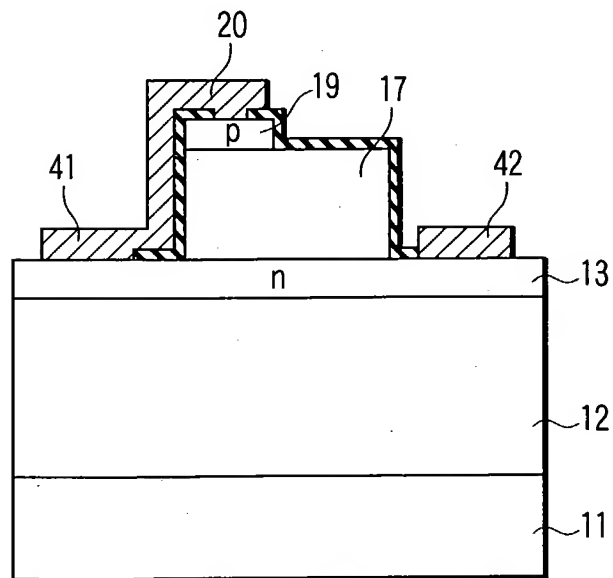


FIG. 24